

ST2001HI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

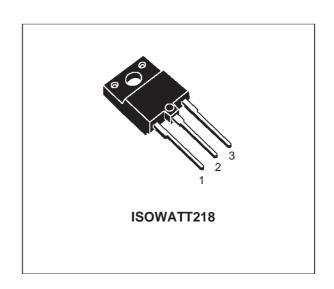
- NEW SERIES, ENHANCHED PERFORMANCE
- FULLY INSULATED PACKAGE FOR EASY MOUNTING
- HIGH VOLTAGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS

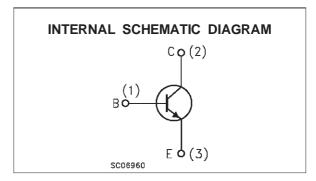
APPLICATIONS:

 HORIZONTAL DEFLECTION FOR COLOR TV AND MONITOR

DESCRIPTION

The ST2001HI is manufactured using Diffused Collector technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	1500	V
Vceo	Collector-Emitter Voltage (I _B = 0)	600	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	7	V
Ic	Collector Current	10	Α
I _{CM}	Collector Peak Current (t _p < 5 ms)	20	Α
lΒ	Base Current	7	Α
P _{tot}	Total Dissipation at T _c = 25 °C	55	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

November 1999 1/6

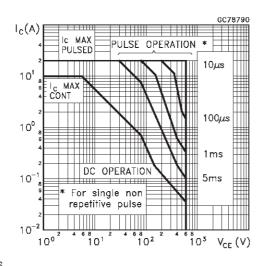
THERMAL DATA

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

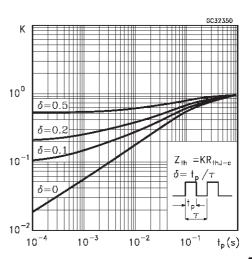
Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1500 V V _{CE} = 1500 V	T _j = 125 °C			1 2	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 7 V				1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	L = 25 mH	600			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 5 A	I _B = 1.25 A			1.5	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 5 A	I _B = 1.25 A			1.2	V
h _{FE} *	DC Current Gain	I _C = 6 A	V _{CE} = 5 V	5		10	
t _s	INDUCTIVE LOAD Storage Time Fall Time	I _C = 5 A L _B = 1 μH f = 64 KHz	$I_{Bon(END)} = 1 A$ $V_{BB} = -2.5 V$		2.5 0.3	3.5 0.45	μs μs

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area

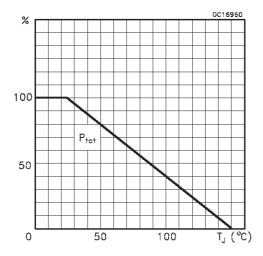


Thermal Impedance

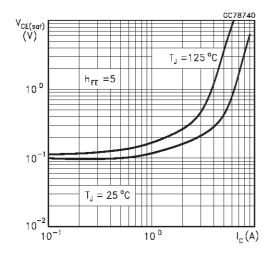


47

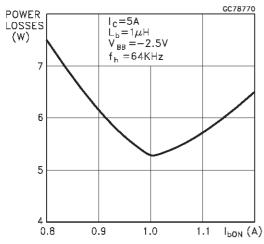
Derating Curve



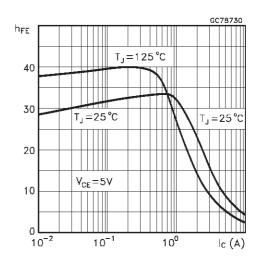
Collector Emitter Saturation Voltage



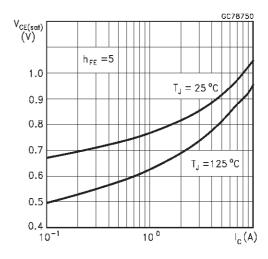
Power Losses



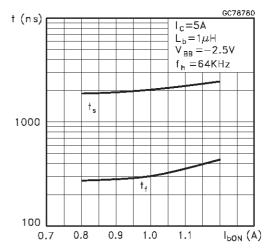
DC Current Gain



Base Emitter Saturation Voltage

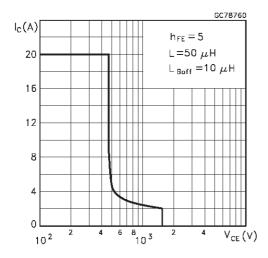


Switching Time Inductive Load

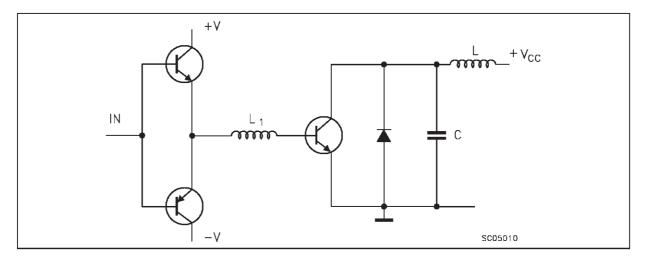


4

RBSOA



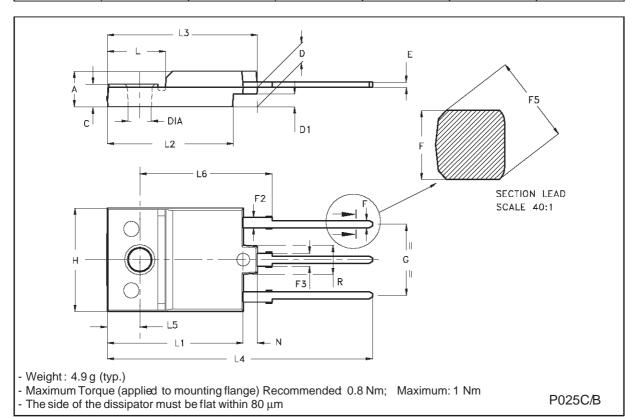
Inductive Load Switching Test Circuits.



4/6

ISOWATT218 NARROW LEADS MECHANICAL DATA

DIM.	mm			inch			
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	5.35		5.65	0.211		0.222	
С	3.30		3.80	0.130		0.150	
D	2.90		3.10	0.114		0.122	
D1	1.88		2.08	0.074		0.082	
Е	0.75		0.95	0.030		0.037	
F	0.75		0.95	0.030		0.037	
F2	1.50		1.70	0.059		0.067	
F3	1.90		2.10	0.075		0.083	
F5			1.10			0.043	
G	10.80		11.20	0.425		0.441	
Н	15.80		16.20	0.622		0.638	
L		9			0.354		
L1	20.80		21.20	0.819		0.835	
L2	19.10		19.90	0.752		0.783	
L3	22.80		23.60	0.898		0.929	
L4	40.50		42.50	1.594		1.673	
L5	4.85		5.25	0.191		0.207	
L6	20.25		20.75	0.797		0.817	
N	2.1		2.3	0.083		0.091	
R		4.6			0.181		
DIA	3.5		3.7	0.138		0.146	



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577